December 2013



FCB20N60F F085

N-Channel MOSFET 600V, **20A**, **190m**Ω

Features

- Typ $r_{DS(on)}$ = 171 $m\Omega$ at V_{GS} = 10V, I_D = 20A
- Typ $Q_{g(tot)}$ = 78nC at V_{GS} = 10V, I_D = 20A
- UIS Capability
- RoHS Compliant
- Qualified to AEC Q101

Description

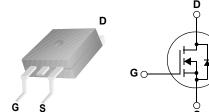
 $\label{eq:superFET} \textbf{SuperFET}^{\text{TM}} \ \text{is Fairchild's proprietary new generation of high}$ voltage MOSFETs utilizing an advanced charge balance mechanism for outstanding low on-resistance and lower gate charge performance.

This advanced technology has been tailored to minimize conduction loss, provide superior switching performance, and withstand extreme dv/dt rate and higher avalanche energy. Consequently, SuperFET is suitable for various automotive



DC/DC power conversion.

- Automotive On Board Charger
- Automotive DC/DC converter for HEV







MOSFET Maximum Ratings T_J = 25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V _{DSS}	Drain to Source Voltage		600	V
V _{GS}	Gate to Source Voltage		±30	V
-	Drain Current - Continuous (V _{GS} =10) (Note 1)	T _C = 25°C	20	۸
ID	Pulsed Drain Current	T _C = 25°C	See Figure4	Α
E _{AS}	Single Pulse Avalanche Energy	(Note 2)	217.8	mJ
D	Power Dissipation		405	W
P_{D}	Derate above 25°C		2.7	W/°C
T _J , T _{STG}	Operating and Storage Temperature		-55 to + 150	°C
$R_{\theta JC}$	Thermal Resistance Junction to Case		0.37	°C/W
$R_{\theta JA}$	Maximum Thermal Resistance Junction to Ambient	(Note 3)	43	°C/W

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FCB20N60F	FCB20N60F_F085	TO-263AB	330mm	24mm	800 units

- 1: Current is limited by bondwire configuration.
- 2: Starting $T_J = 25^{\circ}$ C, L = 10mH, $I_{AS} = 6.6$ A, $V_{DD} = 100$ V during inductor charging and $V_{DD} = 0$ V during time in avalanche
- 3: R_{0.1A} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta JA}$ is determined by the user's board design. The maximum rating presented here is based on mounting on a 1 in² pad of 2oz copper.

Units

nΑ

Electrical Characteristics $T_J = 25^{\circ}C$ unless otherwise noted

Parameter

Gate to Source Leakage Current

Off Cha	Off Characteristics						
B _{VDSS}	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V$	600	-	-	V	
	Drain to Source Leakage Current	$V_{DS} = 600V$, $T_J = 25^{\circ}C$	-	-	10	μΑ	
I _{DSS} Drain to Source Leakag	Drain to Source Leakage Current	$V_{00} = 0V$ $T_{1} = 150^{\circ}C(Note 4)$		_	500	пΔ	

 $V_{GS} = \pm 30V$

Test Conditions

Min

Тур

Max

±100

On Characteristics

Symbol

V _{GS(th)}	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250 \mu A$		3.0	4.3	5.0	V
r Dr	r _{DS(on)} Drain to Source On Resistance	I _D = 20A,	$T_{J} = 25^{\circ}C$	-	171	195	$m\Omega$
DS(on)		V _{GS} = 10V	$T_J = 150^{\circ}C(Note 4)$	-	444	511	$m\Omega$

Dynamic Characteristics

C _{iss}	Input Capacitance	$V_{DS} = 25V, V_{GS} = 0V,$ f = 1MHz		-	2305	-	pF
C _{oss}	Output Capacitance			-	1310	-	pF
C _{rss}	Reverse Transfer Capacitance			-	105	-	pF
R_g	Gate Resistance	f = 1MHz		-	0.95	-	Ω
$Q_{g(ToT)}$	Total Gate Charge at 10V	V_{GS} = 0 to 10V	V _{DD} = 300V	-	78	102	nC
$Q_{g(th)}$	Threshold Gate Charge	V_{GS} = 0 to 2V	I _D = 20A	-	6.6	8.6	nC
Q_{gs}	Gate to Source Gate Charge		_	-	13.8	-	nC
Q_{gd}	Gate to Drain "Miller" Charge			-	41.5	-	nC

Switching Characteristics

t _{on}	Turn-On Time	V_{DD} = 300V, I_{D} = 20A, V_{GS} = 10V, R_{G} = 25 Ω	-	-	176	ns
t _{d(on)}	Turn-On Delay Time		-	43	-	ns
t _r	Rise Time		-	66	-	ns
t _{d(off)}	Turn-Off Delay Time		-	211	-	ns
t _f	Fall Time		-	42	-	ns
t _{off}	Turn-Off Time		-	-	403	ns

Drain-Source Diode Characteristics

V_{SD}	Source to Drain Diode Voltage	$I_{SD} = 20A, V_{GS} = 0V$	1	1.4	V
T _{rr}	Reverse Recovery Time	$I_F = 20A$, $dI_{SD}/dt = 100A/\mu s$,	163	1	ns
Q _{rr}	Reverse Recovery Charge	V _{DD} =480V	1285	1	nC

Notes:

4: The maximum value is specified by design at T_J = 150°C. Product is not tested to this condition in production.

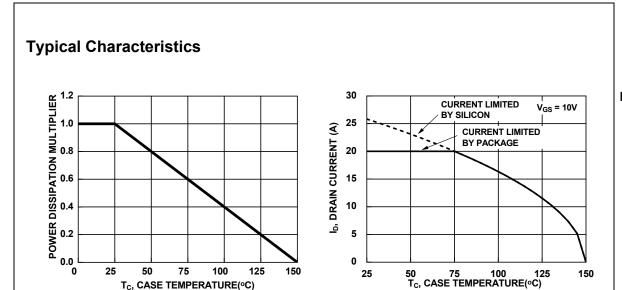
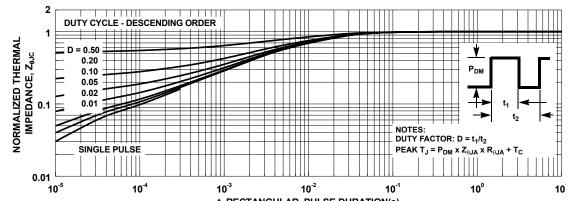


Figure 1. Normalized Power Dissipation vs Case **Temperature**

T_C, CASE TEMPERATURE(°C)

Figure 2. Maximum Continuous Drain Current vs **Case Temperature**



t, RECTANGULAR PULSE DURATION(s)
Figure 3. Normalized Maximum Transient Thermal Impedance

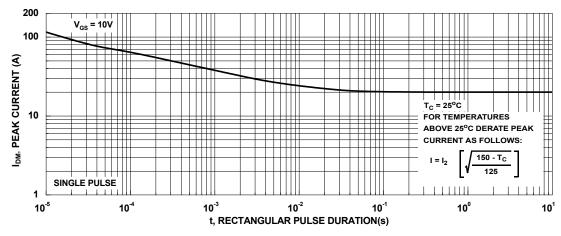
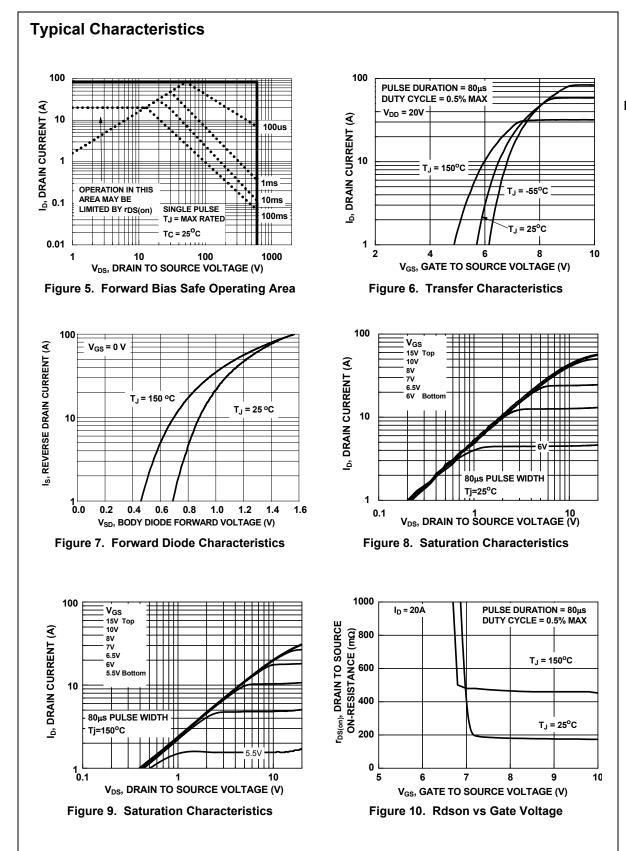
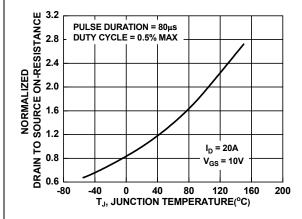


Figure 4. Peak Current Capability



Typical Characteristics



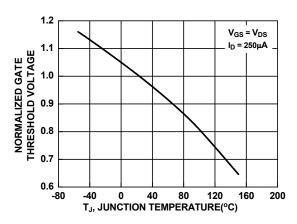
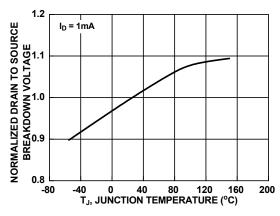
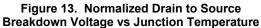


Figure 11. Normalized Rdson vs Junction Temperature

Figure 12. Normalized Gate Threshold Voltage vs
Temperature





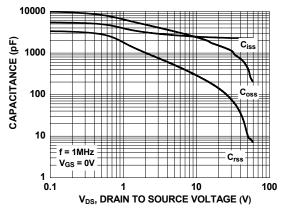


Figure 14. Capacitance vs Drain to Source Voltage

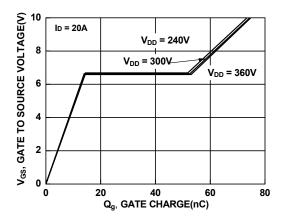


Figure 15. Gate Charge vs Gate to Source Voltage





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